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## High Seebeck coefficient from isolated oligo-phenyl arrays on single layered graphene *via* stepwise assembly†

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Organic thin films composed of highly ordered molecular arrays hold tremendous potential for thermoelectric energy harvesting. In comparison to metal–thiolate arrays formed through covalent bonding, molecular arrays bound to graphene substrates *via* non-covalent interactions exhibit superior thermoelectric behavior. Recent studies have explored the thermoelectric properties of non-conjugated junctions utilizing graphene as a substrate. However, for energy-harvesting purposes, conjugated oligo-aromatic molecules with narrower HOMO–LUMO gaps are more desirable. The step-wise assembly strategy, which involves using a zinc-centered porphyrin to form a footpad first and subsequently binding the molecular backbones to the regularly arranged zinc centers in the footpad, has been reported as an effective approach for growing conjugated molecular backbone arrays, with minimal intermolecular effects on various types of substrates. In this study, we employ this strategy to fabricate aromatic molecular arrays on graphene substrates. Initially, a zinc-centered porphyrin layer is immobilized onto the graphene substrate through  $\pi$ – $\pi$  stacking interactions. Subsequently, a conjugated pyridine backbone is coordinated to the zinc tetraphenylporphyrin (ZnTPP). Due to the substantial footprint of ZnTPP, this sequential assembly method effectively separates the molecular backbones and prevents smearing of the density of states arising from intermolecular interactions. Consequently, a significant enhancement in thermopower is achieved. Our findings present a novel approach for designing high-efficiency thermoelectric materials, resulting in a Seebeck coefficient of approximately  $51 \mu\text{V K}^{-1}$ . This value surpasses the majority of reported Seebeck coefficients for organic molecular junctions.

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## Introduction

Molecular-scale junctions, which utilize molecules as building blocks,<sup>1</sup> offer the potential to revolutionize various technological applications, including transistors,<sup>2–4</sup> sensors,<sup>5</sup> memories,<sup>6</sup> and thermoelectric energy harvesters.<sup>7–9</sup> The electric and thermoelectric properties of molecular junctions have been

extensively investigated in recent years, both at the level of individual molecules<sup>10–13</sup> and self-assembled monolayers (SAMs).<sup>14–16</sup> These studies have predominantly focused on noble-metal substrates like gold, silver, and platinum, together with organic molecular backbones, with specific anchor groups, such as thiolate,<sup>17–19</sup> pyridine, fullerene,<sup>20,21</sup> and large  $\pi$  systems.<sup>22,23</sup> These anchor groups bind to a metallic substrate and facilitate the spontaneous formation of molecular layers on the substrate. Furthermore, the coupling strength between anchor group and substrate plays a crucial role in determining the quantum transport properties of the junction.<sup>7,16,24</sup>

In thermoelectric energy harvesters, it is often desirable to have weak coupling between the anchor group and substrate. This weak coupling serves to effectively suppress interfacial phonon transport<sup>25</sup> and prevent the broadening of molecular frontier orbitals, thereby significantly enhancing the thermoelectric conversion efficiency.<sup>26–28</sup> Metallic substrates have the capability to form weak-coupling junctions with molecules through non-covalent interactions. However, these junctions are inherently unstable at room temperature, due to the high

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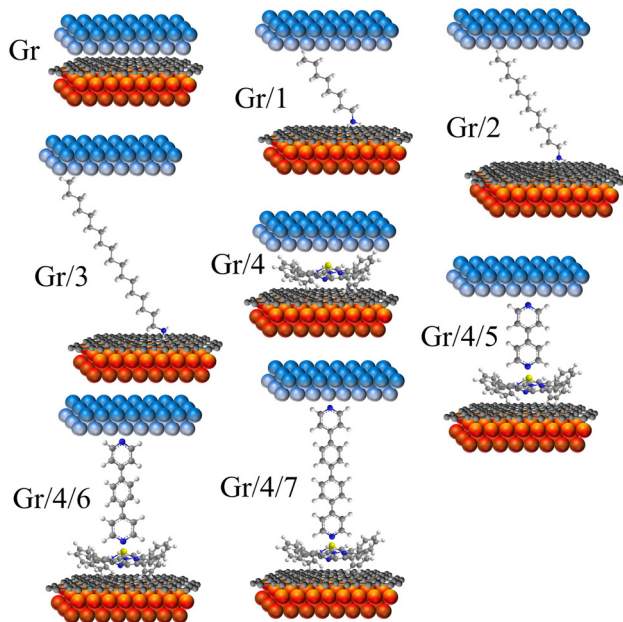


Fig. 2 8 junctions studied in this work. Monolayers including: Gr, Gr/1, Gr/2, Gr/3 and Gr/4. Bilayers including Gr/4/5, Gr/4/6 and Gr/4/7.

electrode.<sup>48</sup> EGaIn is a moldable non-Newtonian liquid metal. In this study, it was shaped into a cone-shaped tip, and the tip retained its shape due to the formation of a  $\sim 0.7$  nm native oxide outer shell (GaOx) upon contact with air.<sup>49,50</sup> It has been proved that this type of tip can contact non-destructively with SAMs,<sup>8–52</sup> and form Cu/Gr/SAMs/GaOx/EGaIn junction.

Fig. S51(a) (ESI<sup>†</sup>) depicts semi-log plots of current density versus bias voltage ( $J$ - $V$ ) curves for a series of Cu/graphene/ $\text{NH}_2\text{-C}_x\text{H}_{x+2}$ /GaO<sub>x</sub>/EGaIn junctions (SAMs 1–3). The  $J$ - $V$  characteristics for each type of SAM were collected from at least 80  $J$ - $V$  curves obtained on at least two independent samples prepared using the same method. Due to the large HOMO–LUMO gap of the alkyl backbones, electron transport in the junction occurs *via* coherent tunneling.<sup>53</sup> Fig. 3(a) illustrates the statistical distribution of conductances ( $G$ ) at zero bias, derived from numerical differentiation for different alkyl linker junctions. The conductance value exponentially decreases with an increase in the number of CH<sub>2</sub> units, as evidenced by the conductance–bias voltage ( $G$ - $V$ ) curves shown in Fig. S52(a) (ESI<sup>†</sup>).

One of the major challenges encountered when studying molecular transport using the EGaIn method is the significantly smaller effective electric contact area between the EGaIn tip and the SAMs layer compared to the physical contact area. Hence, accurately estimating the absolute conductivity of the SAM is difficult.<sup>54</sup> In this study, a unitless relative conductivity was employed instead of absolute conductivity. The measured contact conductivity of Cu/graphene/Ga<sub>2</sub>O<sub>3</sub>/EGaIn was assigned a value of 1, and the conductivity of all the junctions was expressed relative to this value. The absolute conductivity values for all the junctions (in  $\text{S cm}^{-2}$ ) are listed in Table S1 (ESI<sup>†</sup>).

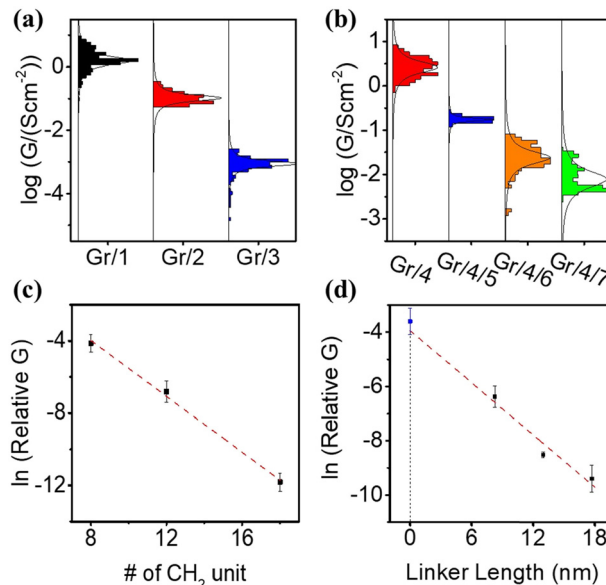


Fig. 3 (a)  $G$ - $V$  curve of Gr/SAMs/GaOx/EGaIn junction, SAMs molecule: **1**, **2** and **3**; (b)  $G$ - $V$  curve of Gr/SAMs/GaOx/GaIn junction, SAMs molecule: **4**, **4/5**, **4/6** and **4/7**. (c) Plot of  $\ln(G)$  vs. number of alkyl unit for SAM **1**–**3**. (d) Plot of  $\ln(G)$  vs. linker length for SAM **4**, **4/5**, **4/6** and **4/7**. Note relative conductance (relative  $G$ ) is used in (c) and (d), the definition of relative  $G$  is explained in main text.

Fig. 3(c) shows a plot of  $\ln(G)$  vs. the numbers of CH<sub>2</sub> units. The linear relationship between  $\ln(G)$  and molecular length confirms that transport is in the tunneling regime *via* expression:

$$\ln(G) = \ln(G_0) - \beta d$$

$G$  the measured conductance,  $G_0$  the contact conductance at  $d = 0$ ,  $d$  is the molecular length and  $\beta$  the tunneling decay factor related with tunneling barrier height.<sup>55,56</sup> The calculated  $\beta$  value was  $0.8 \pm 0.2$  per alkyl unit. This value is comparable with, but slightly lower than, reported experimental and theoretical values on single molecule junctions with similar structures (0.9–1 per alkyl unit),<sup>57</sup> which could be due to the presence of defects in the SAMs.<sup>58</sup>

The fitted relative contact conductivity at  $d = 0$  ( $G_0$ ) for alkyl-based SAMs on graphene was determined to be  $9.0 \pm 3.4$ . This value represents an order of magnitude increase compared to the measured contact conductivity (1). We attribute this difference to the complex contact interface between EGaIn and graphene, as the measurements were conducted under ambient conditions where contaminants, such as a thin film of water, can significantly reduce the measured current. In contrast, SAMs on graphene do not exhibit this issue due to their hydrophobic nature, which protects the surface from water contamination. As a result, SAM-modified graphene provides a more uniform contact and yields higher contact conductance.<sup>59</sup>

The electric behavior of the multi-component conjugated SAM-based junctions Gr/4/5, Gr/4/6 and Gr/4/7 were measured, with statistical results obtained from 80  $J$ - $V$  curves achieved on at least 2 independent samples (Fig. S51(b), ESI<sup>†</sup>). The corresponding



















